

# Elvedin Memisevic

## List of Publications by Year in descending order

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24  
papers

579  
citations

840776

11  
h-index

940533

16  
g-index

24  
all docs

24  
docs citations

24  
times ranked

642  
citing authors

#	ARTICLE	IF	CITATIONS
1	Individual Defects in InAs/InGaAsSb/GaSb Nanowire Tunnel Field-Effect Transistors Operating below 60 mV/decade. Nano Letters, 2017, 17, 4373-4380.	9.1	85
2	High-Frequency Gate-All-Around Vertical InAs Nanowire MOSFETs on Si Substrates. IEEE Electron Device Letters, 2014, 35, 518-520.	3.9	77
3	Nanowire Tunnel FET with Simultaneously Reduced Subthermionic Subthreshold Swing and Off-Current due to Negative Capacitance and Voltage Pinning Effects. Nano Letters, 2020, 20, 3255-3262.	9.1	58
4	Scaling of Vertical InAs/GaSb Nanowire Tunneling Field-Effect Transistors on Si. IEEE Electron Device Letters, 2016, 37, 549-552.	3.9	56
5	III-V Heterostructure Nanowire Tunnel FETs. IEEE Journal of the Electron Devices Society, 2015, 3, 96-102.	2.1	53
6	InAs/InGaAsSb/GaSb Nanowire Tunnel Field-Effect Transistors. IEEE Transactions on Electron Devices, 2017, 64, 4746-4751.	3.0	53
7	Vertical InAs/GaAsSb/GaSb tunneling field-effect transistor on Si with $S = 48$ mV/decade and $I_{on}/I_{off} = 10^4$ at $V_{ds} = 0.3$ V. , 2016, , .		45
8	Vertical Nanowire TFETs With Channel Diameter Down to 10 nm and Point S <sub>MIN</sub> of 35 mV/Decade. IEEE Electron Device Letters, 2018, 39, 1089-1091.	3.9	35
9	Impact of Band-Tails on the Subthreshold Swing of III-V Tunnel Field-Effect Transistor. IEEE Electron Device Letters, 2017, 38, 1661-1664.	3.9	23
10	Low-Frequency Noise in III-V Nanowire TFETs and MOSFETs. IEEE Electron Device Letters, 2017, 38, 1520-1523.	3.9	19
11	Impact of source doping on the performance of vertical InAs/InGaAsSb/GaSb nanowire tunneling field-effect transistors. Nanotechnology, 2018, 29, 435201.	2.6	12
12	Single-Shot Fabrication of Semiconducting-Superconducting Nanowire Devices. Advanced Functional Materials, 2021, 31, 2102388.	14.9	12
13	Tuning of Source Material for InAs/InGaAsSb/GaSb Application-Specific Vertical Nanowire Tunnel FETs. ACS Applied Electronic Materials, 2020, 2, 2882-2887.	4.3	11
14	An Experimental Study of Heterostructure Tunnel FET Nanowire Arrays: Digital and Analog Figures of Merit from 300K to 10K. , 2018, , .		10
15	Thin electron beam defined hydrogen silsesquioxane spacers for vertical nanowire transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, 051211.	1.2	8
16	The impact of hetero-junction and oxide-interface traps on the performance of InAs/Si and InAs/GaAsSb nanowire tunnel FETs. , 2017, , .		5
17	Capacitance Measurements in Vertical III-V Nanowire TFETs. IEEE Electron Device Letters, 2018, 39, 943-946.	3.9	5
18	Molybdenum nanopillar arrays: Fabrication and engineering. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 134, 114903.	2.7	5

#	ARTICLE	IF	CITATIONS
19	Impact of Non-idealities on the Performance of InAs/(In)GaAsSb/GaSb Tunnel FETs. Composants Nano-Electroniques, 2018, 18, .	0.2	4
20	Random telegraph signal noise in tunneling field-effect transistors with S below 60 mV/decade. , 2017, .		2
21	RF characterization of vertical InAs nanowire MOSFETs with $f_{t}$ and $f_{max}$ above 140 GHz. , 2014, , .		1
22	Projected performance of experimental InAs/GaAsSb/GaSb TFET as millimeter-wave detector. , 2017, , .		0
23	Trap-Aware Compact Modeling and Power-Performance Assessment of III-V Tunnel FET. , 2018, , .		0
24	Effect of Gate Oxide Defects on Tunnel Transistor RF Performance. , 2018, , .		0